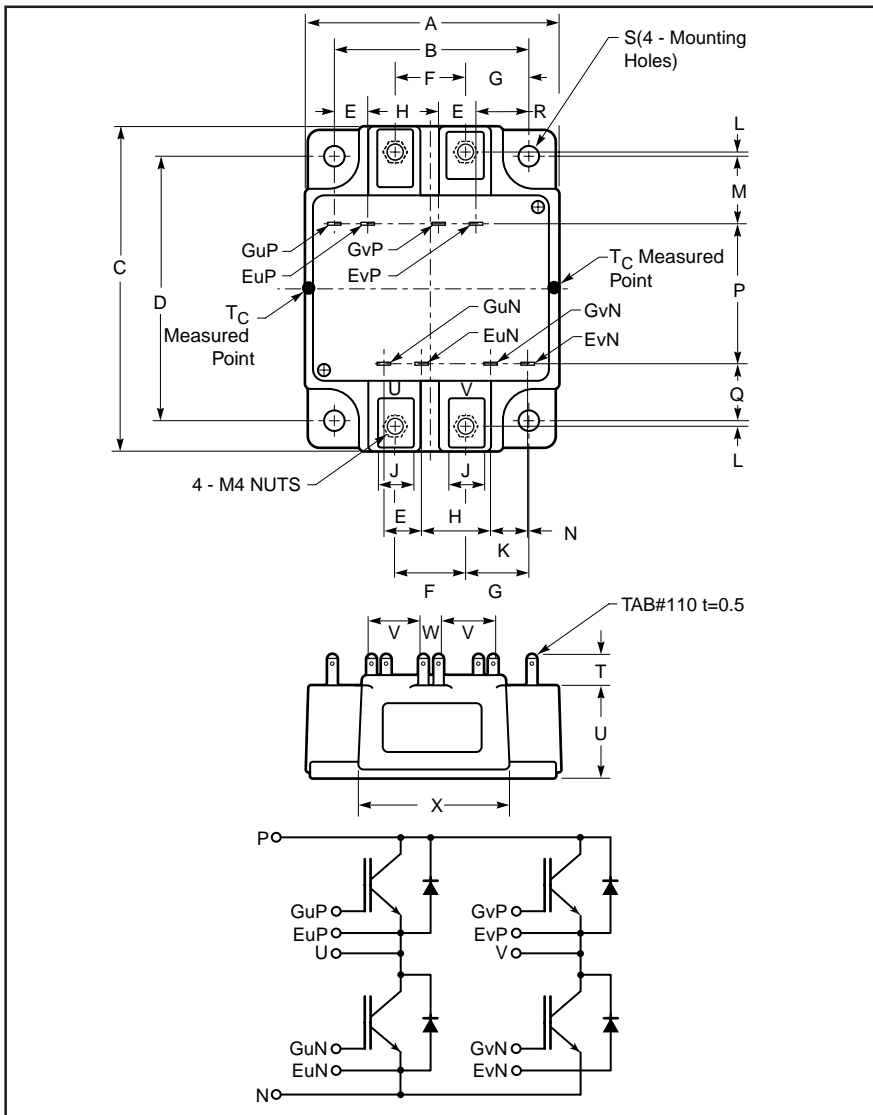


# MITSUBISHI IGBT MODULES

## CM100BU-12H

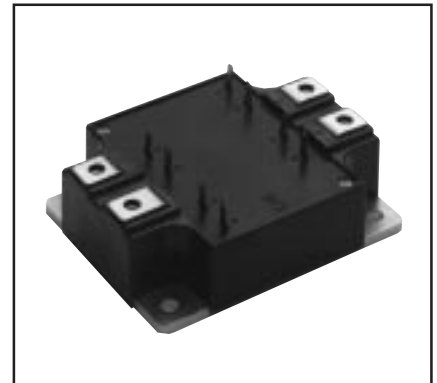
HIGH POWER SWITCHING USE  
INSULATED TYPE



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	2.83	72.0
B	2.17±0.01	55±0.25
C	3.58	91.0
D	2.91±0.01	74.0±0.25
E	0.43	11.0
F	0.79	20.0
G	0.69	17.5
H	0.75	19.1
J	0.39	10.0
K	0.41	10.5
L	0.05	1.25

Dimensions	Inches	Millimeters
M	0.74	18.7
N	0.02	0.5
P	1.55	39.3
Q	0.63	16.0
R	0.57	14.4
S	0.22 Dia.	5.5 Dia.
T	0.32	8.1
U	1.02	26.0
V	0.59	15.0
W	0.20	5.0
X	1.61	41.0



### Description:

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of four IGBTs in an H-Bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

### Features:

- Low Drive Power
- Low  $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- High Frequency Operation
- Isolated Baseplate for Easy Heat Sinking

### Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies

### Ordering Information:

Example: Select the complete module number you desire from the table - i.e. CM100BU-12H is a 600V ( $V_{CES}$ ), 100 Ampere Four-IGBT Module.

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	100	12

## CM100BU-12H

HIGH POWER SWITCHING USE  
INSULATED TYPEAbsolute Maximum Ratings,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

	Symbol	Ratings	Units
Junction Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	$V_{CES}$	600	Volts
Gate-Emitter Voltage (C-E SHORT)	$V_{GES}$	$\pm 20$	Volts
Collector Current ( $T_c = 25^\circ\text{C}$ )	$I_C$	100	Amperes
Peak Collector Current ( $T_j \leq 150^\circ\text{C}$ )	$I_{CM}$	200*	Amperes
Emitter Current** ( $T_c = 25^\circ\text{C}$ )	$I_E$	100	Amperes
Peak Emitter Current**	$I_{EM}$	200*	Amperes
Maximum Collector Dissipation ( $T_c = 25^\circ\text{C}$ )	$P_C$	400	Watts
Mounting Torque, M4 Main Terminal	–	1.3 ~ 1.7	N · m
Mounting Torque, M5 Mounting	–	2.5 ~ 3.5	N · m
Weight	–	390	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{iso}$	2500	Vrms

\* Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.

\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}, V_{GE} = 0V$	–	–	1	mA
Gate Leakage Voltage	$I_{GES}$	$V_{GE} = V_{GES}, V_{CE} = 0V$	–	–	0.5	$\mu\text{A}$
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 10\text{mA}, V_{CE} = 10V$	4.5	6	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100\text{A}, V_{GE} = 15V, T_j = 25^\circ\text{C}$	–	2.4	3.0	Volts
		$I_C = 100\text{A}, V_{GE} = 15V, T_j = 125^\circ\text{C}$	–	2.6	–	Volts
Total Gate Charge	$Q_G$	$V_{CC} = 300V, I_C = 100\text{A}, V_{GE} = 15V$	–	200	–	nC
Emitter-Collector Voltage*	$V_{EC}$	$I_E = 100\text{A}, V_{GE} = 0V$	–	–	2.6	Volts

\* Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.Dynamic Electrical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	$C_{ies}$		–	–	8.8	nF
Output Capacitance	$C_{oes}$	$V_{CE} = 10V, V_{GE} = 0V$	–	–	4.8	nF
Reverse Transfer Capacitance	$C_{res}$		–	–	1.3	nF
Resistive	Turn-on Delay Time	$V_{CC} = 300V, I_C = 100\text{A},$ $V_{GE1} = V_{GE2} = 15V,$	–	–	100	ns
	Rise Time					
Load	Turn-off Delay Time	$R_G = 6.3\Omega, \text{Resistive}$	–	–	200	ns
	Fall Time					
Switch		Load Switching Operation	–	–	300	ns
Diode Reverse Recovery Time	$t_{rr}$	$I_E = 100\text{A}, di_E/dt = -200\text{A}/\mu\text{s}$	–	–	160	ns
Diode Reverse Recovery Charge	$Q_{rr}$	$I_E = 100\text{A}, di_E/dt = -200\text{A}/\mu\text{s}$	–	0.24	–	$\mu\text{C}$

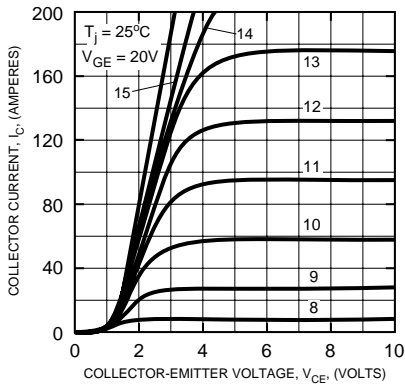
Thermal and Mechanical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/4 Module	–	–	0.31	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/4 Module	–	–	0.7	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	–	0.025	–	$^\circ\text{C}/\text{W}$

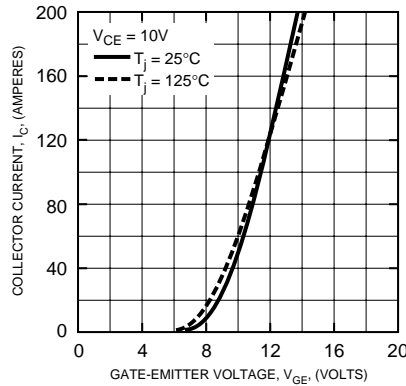
# CM100BU-12H

HIGH POWER SWITCHING USE  
INSULATED TYPE

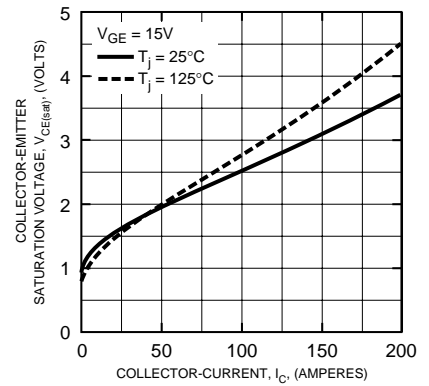
OUTPUT CHARACTERISTICS  
(TYPICAL)



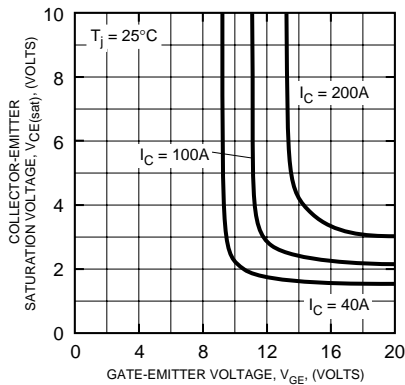
TRANSFER CHARACTERISTICS  
(TYPICAL)



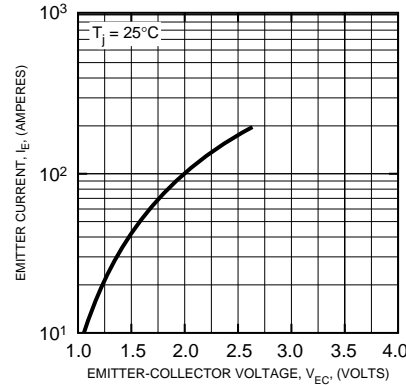
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS  
(TYPICAL)



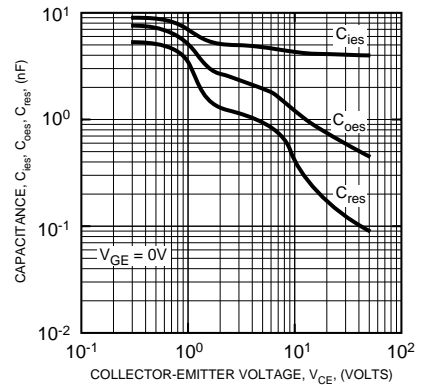
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS  
(TYPICAL)



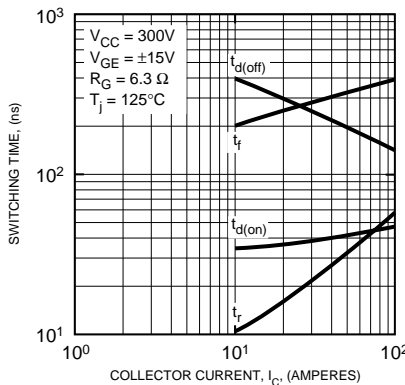
FREE-WHEEL DIODE FORWARD CHARACTERISTICS  
(TYPICAL)



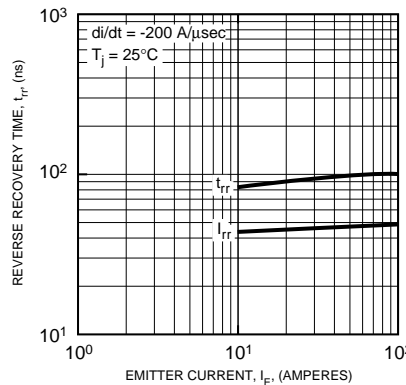
CAPACITANCE VS.  $V_{CE}$   
(TYPICAL)



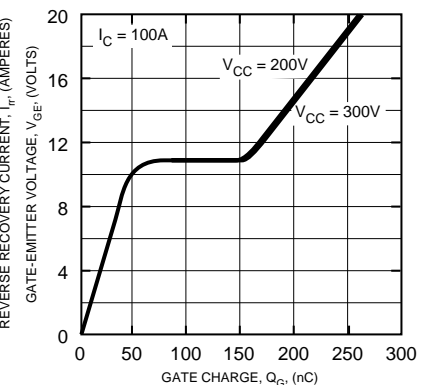
HALF-BRIDGE SWITCHING CHARACTERISTICS  
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS  
(TYPICAL)



GATE CHARGE,  $V_{GE}$



# CM100BU-12H

HIGH POWER SWITCHING USE  
INSULATED TYPE

